

ABSTRACT OF THE DISCLOSURE

A semiconductor pressure sensor device has a fully-filling gel structure including a sensor chip for detecting a pressure and generating an electrical signal corresponding to the pressure. This sensor chip of the sensor device is connected with a conductive member such as a terminal using a bonding wire. The sensor chip and bonding wire are covered by a protective member that has characteristics of electric insulation and plasticity. Here, the bonding wire is formed of an alloy of Au and Pd. This structure using a bonding wire of an Au-Pd alloy enables wire strength to be enhanced without the wire diameter being largely increased in comparison with a conventional one.